

Description

The 30P06 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications. The 30P06 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

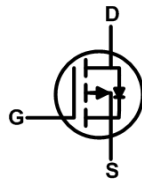
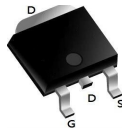
Super Low Gate Charge

100% EAS Guaranteed

Green Device Available

Excellent CdV/dt effect decline

Advanced high cell density Trench technology

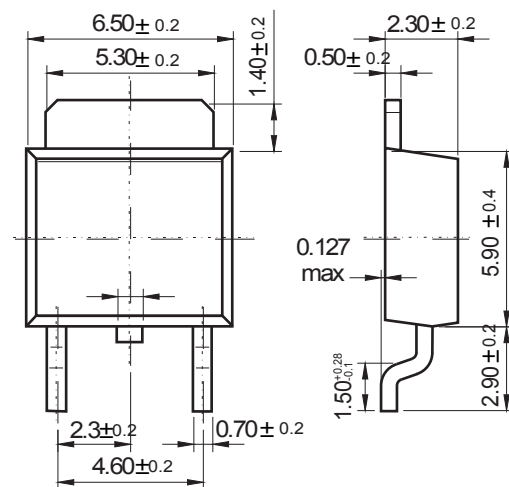


Product Summary

BVDSS	RDSON	ID
-60V	30mΩ	-30A

TO-252

Unit: mm



Dimensions in inches and (millimeters)

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10V^1$	-30	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10V^1$	-12	A
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10V^1$	-4.5	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -10V^1$	-4.0	A
I_{DM}	Pulsed Drain Current ²	-30	A
EAS	Single Pulse Avalanche Energy ³	18.1	mJ
I_{AS}	Avalanche Current	-13	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	25	W
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ⁴	2	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	5	$^\circ\text{C/W}$

30P06

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=-250\mu A$	-60	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=-1mA$	---	-0.023	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V$, $I_D=-10A$	---	30	45	$m\Omega$
		$V_{GS}=-4.5V$, $I_D=-6A$	---	52	60	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=-250\mu A$	-1.2	---	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4	---	$mV/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-24V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	-1	μA
		$V_{DS}=-24V$, $V_{GS}=0V$, $T_J=55^\circ\text{C}$	---	---	-5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
gfs	Forward Transconductance	$V_{DS}=-5V$, $I_D=-15A$	---	12	---	S
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-15V$, $V_{GS}=-4.5V$, $I_D=-15A$	---	6.1	---	nC
Q_{gs}	Gate-Source Charge		---	3.1	---	
Q_{gd}	Gate-Drain Charge		---	1.8	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-15V$, $V_{GS}=-10V$, $R_G=3.3\Omega$, $I_D=-15A$	---	2.6	---	ns
T_r	Rise Time		---	8.6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	33.6	---	
T_f	Fall Time		---	6	---	
C_{iss}	Input Capacitance	$V_{DS}=-15V$, $V_{GS}=0V$, $f=1MHz$	---	585	---	pF
C_{oss}	Output Capacitance		---	100	---	
C_{rss}	Reverse Transfer Capacitance		---	85	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	-20	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	-30	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=-1A$, $T_J=25^\circ\text{C}$	---	---	-1.2	V
t_{rr}	Reverse Recovery Time	$I_F=-15A$, $dI/dt=100A/\mu s$, $T_J=25^\circ\text{C}$	---	6.1	---	nS
Q_{rr}	Reverse Recovery Charge		---	1.4	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=-25V$, $V_{GS}=-10V$, $L=0.1mH$, $I_{AS}=-19A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

RATING AND CHARACTERISTIC CURVES (30P06)

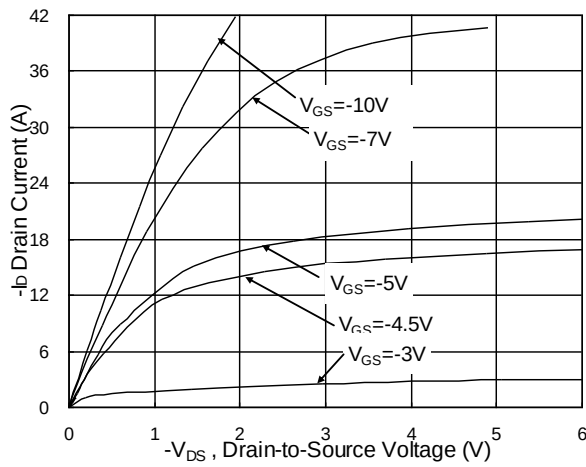


Fig.1 Typical Output Characteristics

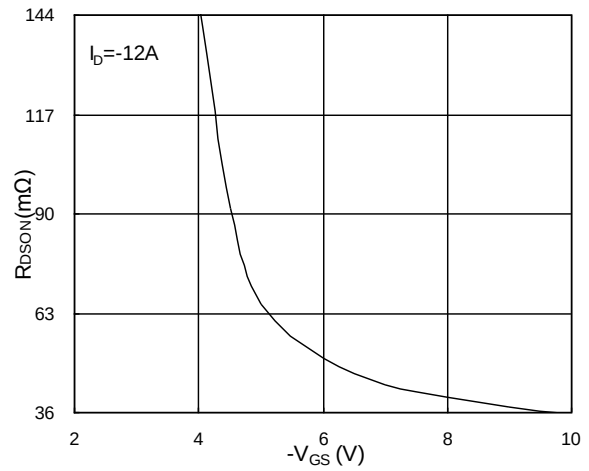


Fig.2 On-Resistance v.s Gate-Source

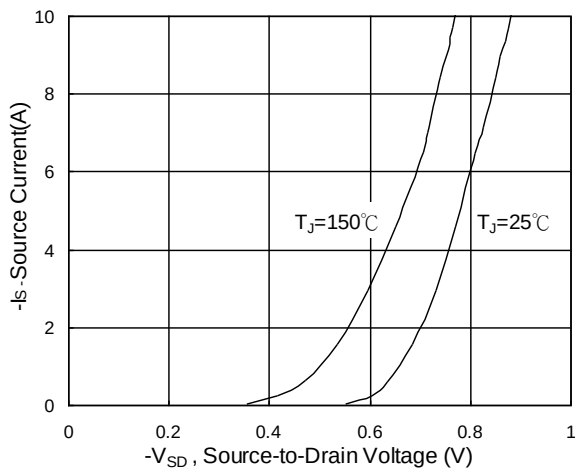


Fig.3 Forward Characteristics Of Reverse

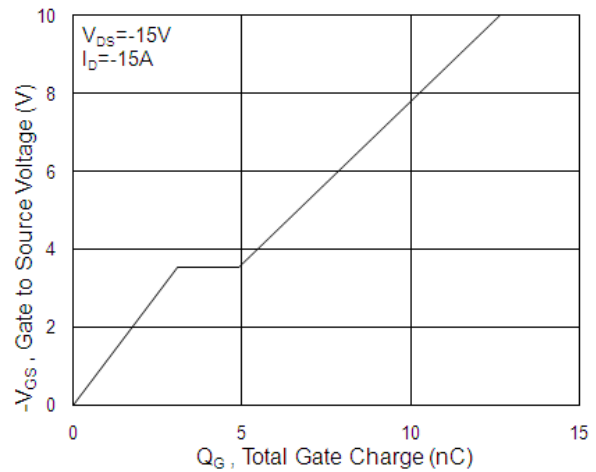


Fig.4 Gate Charge Characteristics

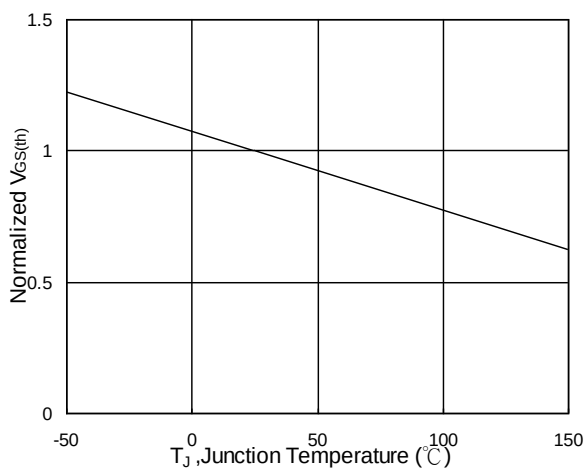


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

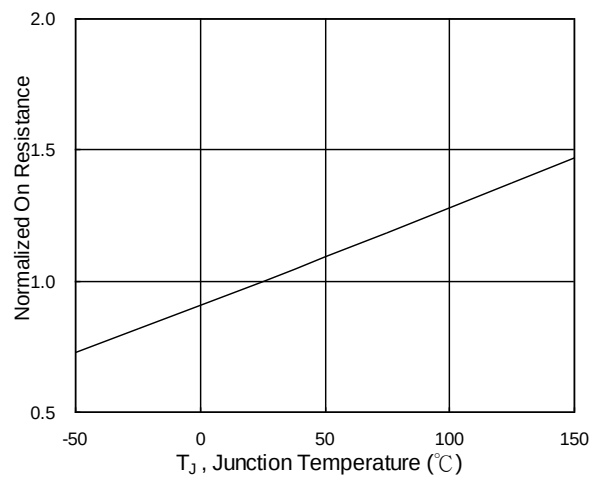
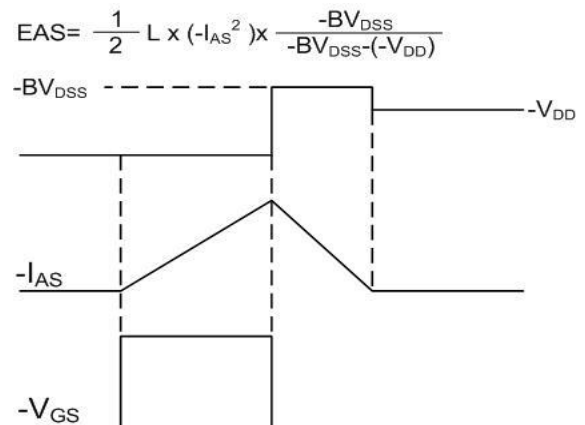
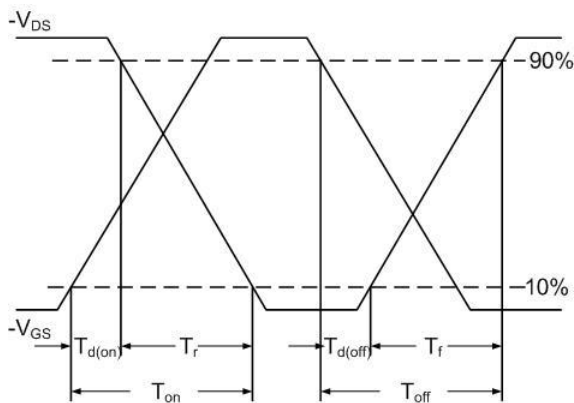
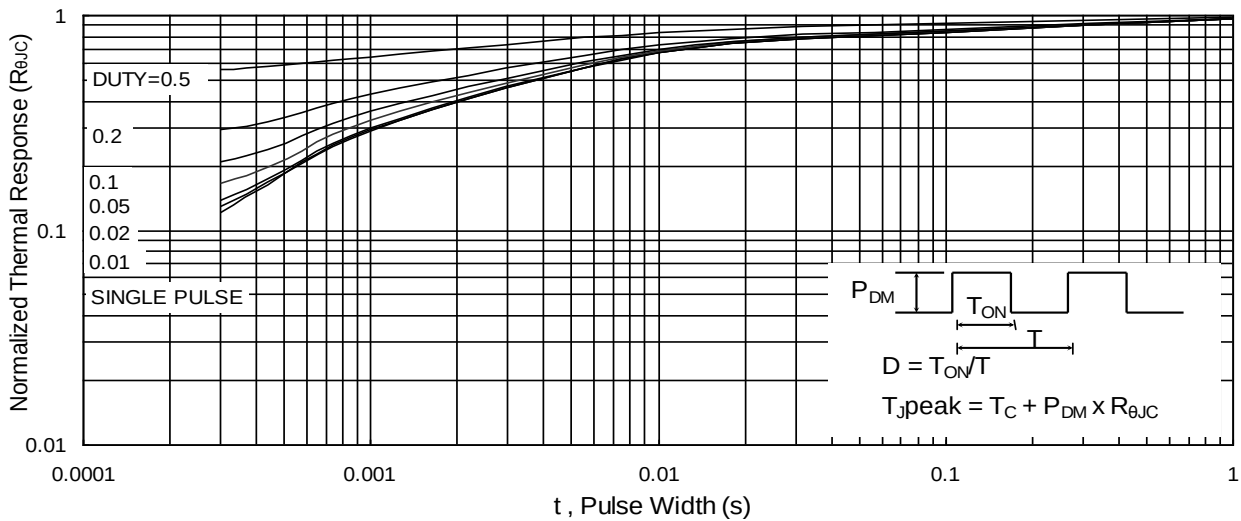
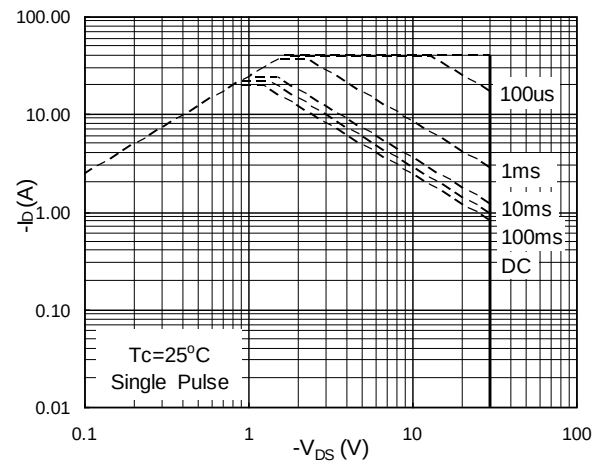
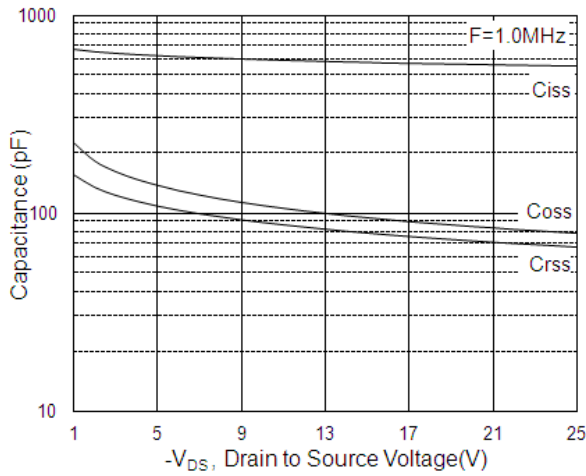


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

RATING AND CHARACTERISTIC CURVES (30P06)



$$EAS = \frac{1}{2} L \times (-I_{AS}^2) \times \frac{-BV_{DSS}}{-BV_{DSS} - (-V_{DD})}$$